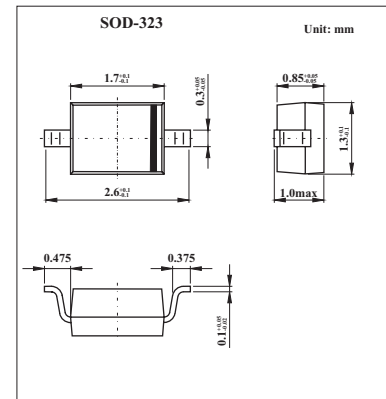


Silicon Epitaxial Planar Diode

1SV287

■ Features

- High Capacitance Ratio: $C_{2V}/C_{25V} = 7.6$ (Typ.)
- Low Series Resistance: $r_s = 1.9 \Omega$ (Typ.)
- Excellent C-V Characteristics, and Small Tracking Error.
- Useful for small size Tuner.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Peak Reverse Voltage	V_{RM}	35 ($R_L = 10 \text{ K } \Omega$)	V
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	V_R	$I_R = 1 \mu\text{A}$	30			V
Reverse Current	I_R	$V_R = 28 \text{ V}$			10	nA
Capacitance	C_{2V}	$f = 1 \text{ MHz}; V_R = 2 \text{ V}$	4.2		5.7	pF
	C_{25V}	$f = 1 \text{ MHz}; V_R = 25 \text{ V}$	0.53		0.68	
Capacitance Ratio	C_{2V}/C_{25V}		7.3			
Series Resistance	r_s	$V_R = 1 \text{ V}, f = 470 \text{ MHz}$		1.9	2.3	Ω

Note :

Available in matched group for capacitance to 6%.

$$\frac{C(\text{Max.}) - C(\text{Min.})}{C(\text{Min.})} \leq 0.06$$

$(V_R = 2 \sim 25 \text{ V})$

■ Marking

Marking	TK
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